LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A power module comprising:

a first lead frame having a first conductive pad;

a first power device disposed on and electrically connected to said first conductive pad; ~~and~~

a first heatsink in thermal contact with said first conductive pad; wherein there is no intermediate body disposed between said first conductive pad and said heatsink that retards heat transference from said first power device to said first heatsink; and

a second lead frame having a second conductive pad, a second power device disposed on and electrically connected to said second conductive pad, and a second heatsink in thermal contact with said second conductive pad, wherein there is no intermediate body between said second conductive pad and said second heatsink that retards heat transference from said second power device to said second heatsink, and wherein said second heatsink is larger than said first heatsink whereby a thermal gradient between said heatsinks may be reduced to reduce thermal stresses on said module.

2. (Original) A power module according to claim 1, further comprising a lead integrally connected to said first conductive pad.

3. (Canceled)

4. (Currently Amended) A power module according to claim [[3]] 1, wherein said first heatsink and said second heatsink are electrically isolated.

5. (Currently Amended) A power module according to claim [[3]] 1, wherein said first heatsink and said second heatsink are disposed within a common frame.

6. (Currently Amended) A power module according to claim [[3]] 1, wherein said first power device and said second power device are arranged to form a half-bridge circuit.

7. (Currently Amended) A power module according to claim [[3]] 1, wherein said first and second power device are power MOSFETs each having its electrode connected electrically to a respective conductive pad.

8. (Currently Amended) A power module according to claim [[3]] 1, wherein said first and second power devices are N-channel power MOSFETs each having its drain electrode electrically connected to a respective conductive pad.

9. (Original) A power module according to claim 8, further comprising a common conductive node, and wherein each of said N-channel power MOSFETs includes a source electrode electrically connected to said common conductive node.

10. (Currently Amended) A power module according to claim [[3]] 1, wherein said first power device is a P-channel power MOSFET and said second power device is an N-channel power MOSFET.

11. A power module according to claim 10, further comprising a common conductive node, and wherein each of said power MOSFETs includes a source electrode electrically connected to said common conductive node.